

## LSE07N65-VB Datasheet

### N-Channel 650V(D-S) Super Junction Power MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	650	
$R_{DS(on)}$ at 25 °C ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.50
$Q_g$ max. (nC)	25	
$Q_{gs}$ (nC)	2.0	
$Q_{gd}$ (nC)	2.7	
Configuration	Single	

#### FEATURES

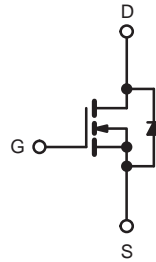
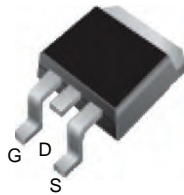
- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)



RoHS

#### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial

D<sup>2</sup>PAK (TO-263)

N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ °C}$ , unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			$V_{DS}$	650	V
Gate-Source Voltage			$V_{GS}$	± 30	
Continuous Drain Current ( $T_J = 150\text{ }^{\circ}\text{C}$ )	$V_{GS}$ at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	9	A
		$T_C = 100\text{ }^{\circ}\text{C}$		6	
Pulsed Drain Current <sup>a</sup>			$I_{DM}$	21	
Linear Derating Factor				1.5	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy <sup>b</sup>			$E_{AS}$	186	mJ
Maximum Power Dissipation			$P_D$	123	W
Operating Junction and Storage Temperature Range			$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$
Drain-Source Voltage Slope	$T_J = 125\text{ }^{\circ}\text{C}$		dV/dt	50	V/ns
Reverse Diode dV/dt <sup>d</sup>				4.5	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s			300	$^{\circ}\text{C}$


#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ °C}$ ,  $L = 28.2\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 3.5\text{ A}$ .
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100\text{ A}/\mu\text{s}$ , starting  $T_J = 25\text{ °C}$ .

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	63	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.6	

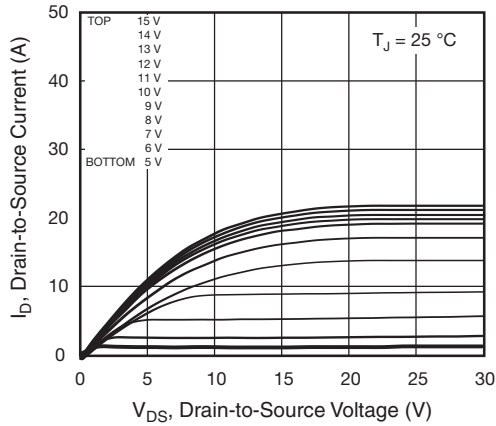
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		650	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.65	-	V/ $^\circ\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 520\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}$	-	0.50	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}$ , $I_D = 4\text{ A}$		-	16	-	S
Dynamic							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$		-	360	-	pF
Output Capacitance	$C_{oss}$			-	25	-	
Reverse Transfer Capacitance	$C_{rss}$			-	12	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}$ , $V_{GS} = 0\text{ V}$		-	45	-	pF
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$			-	62	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}$ , $V_{DS} = 520\text{ V}$	-	25	-	nC
Gate-Source Charge	$Q_{gs}$			-	2.0	-	
Gate-Drain Charge	$Q_{gd}$			-	2.7	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}$ , $I_D = 4\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$		-	25	-	ns
Rise Time	$t_r$			-	55	-	
Turn-Off Delay Time	$t_{d(off)}$			-	70	-	
Fall Time	$t_f$			-	40	-	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}$ , open drain		-	3.5	-	$\Omega$
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	18	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = 4\text{ A}$ , $V_{GS} = 0\text{ V}$		-	-	1.5	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = I_S = 4\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 400\text{ V}$		-	190	-	ns
Reverse Recovery Charge	$Q_{rr}$			-	2.3	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	10	-	A

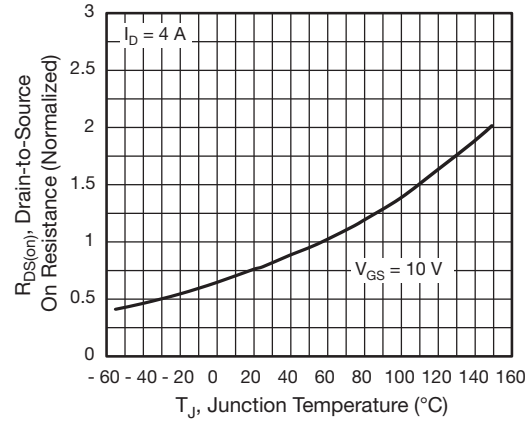
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

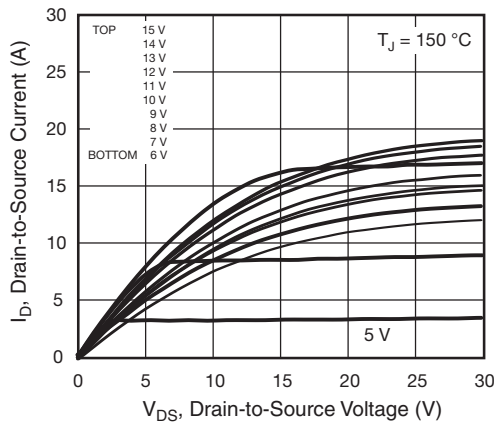
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



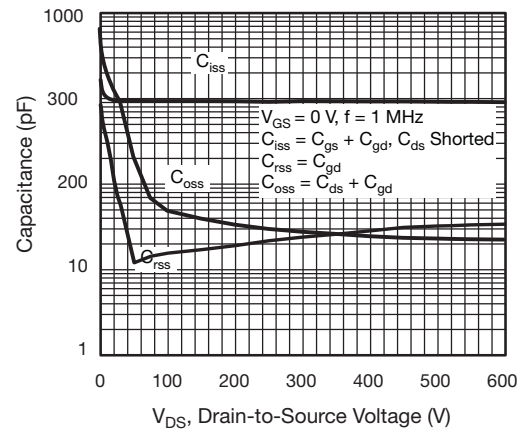
**Fig. 1 - Typical Output Characteristics**



**Fig. 4 - Normalized On-Resistance vs. Temperature**



**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



Fig. 7 - Typical Source-Drain Diode Forward Voltage

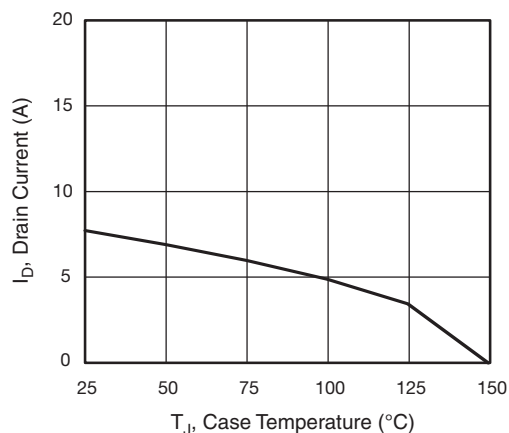


Fig. 9 - Maximum Drain Current vs. Case Temperature

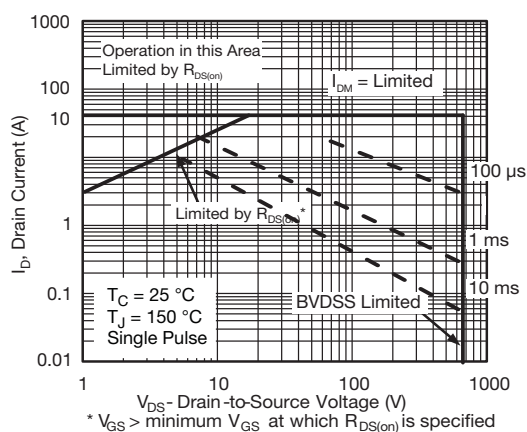


Fig. 8 - Maximum Safe Operating Area



Fig. 10 - Temperature vs. Drain-to-Source Voltage

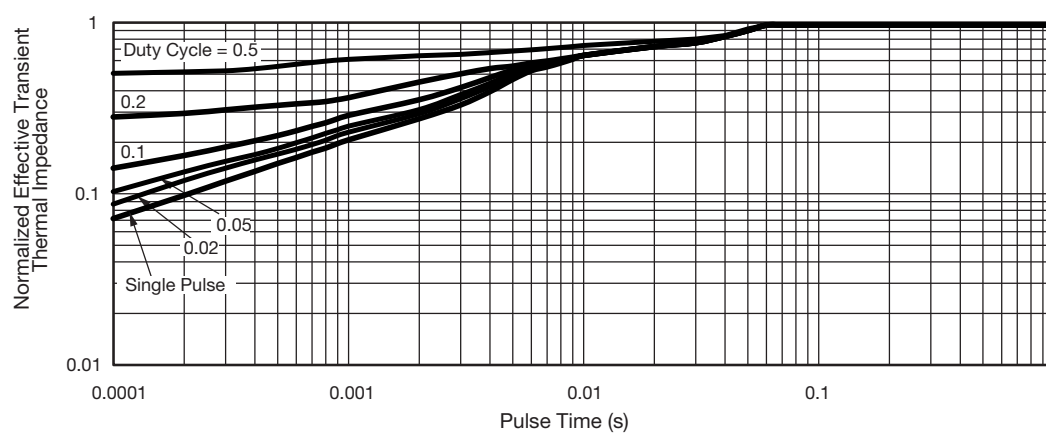


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

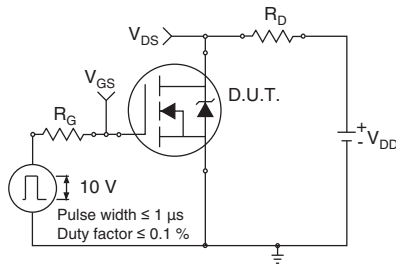


Fig. 12 - Switching Time Test Circuit

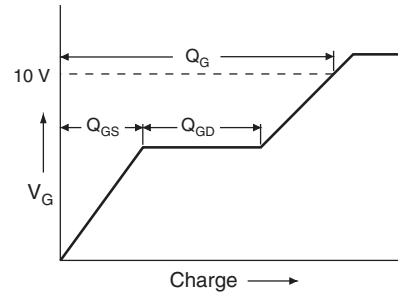


Fig. 16 - Basic Gate Charge Waveform

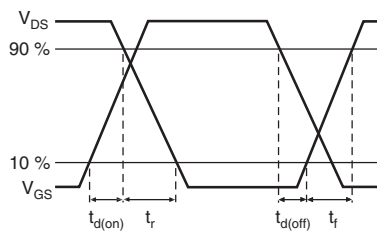


Fig. 13 - Switching Time Waveforms

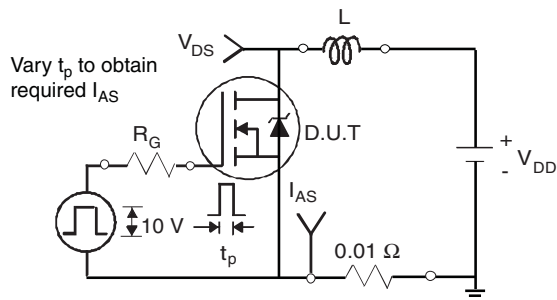


Fig. 14 - Unclamped Inductive Test Circuit

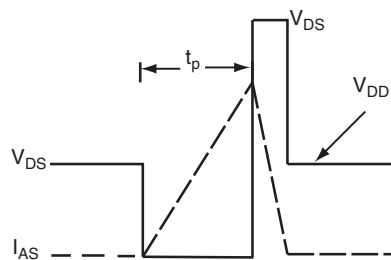


Fig. 15 - Unclamped Inductive Waveforms

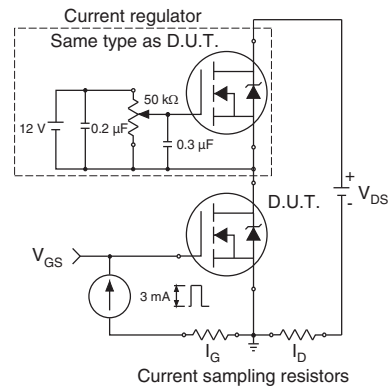
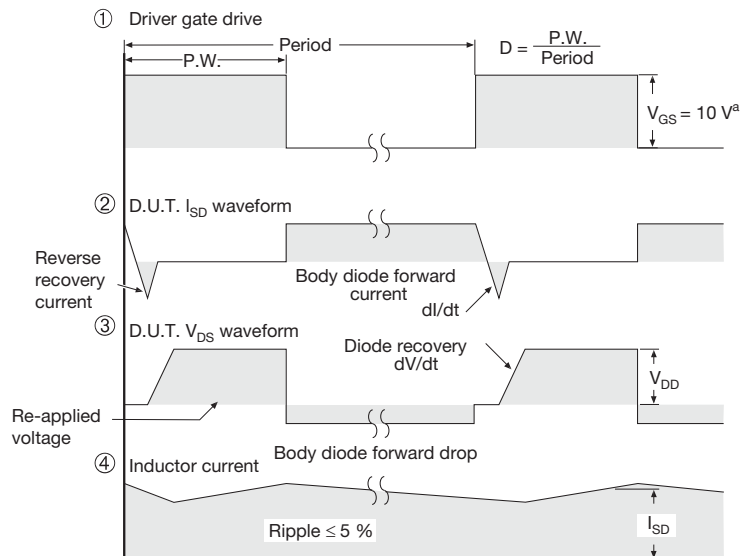
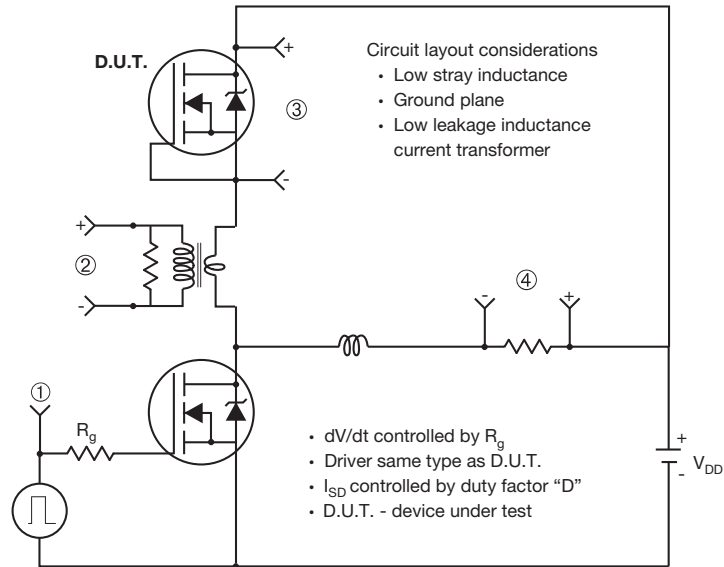


Fig. 17 - Gate Charge Test Circuit

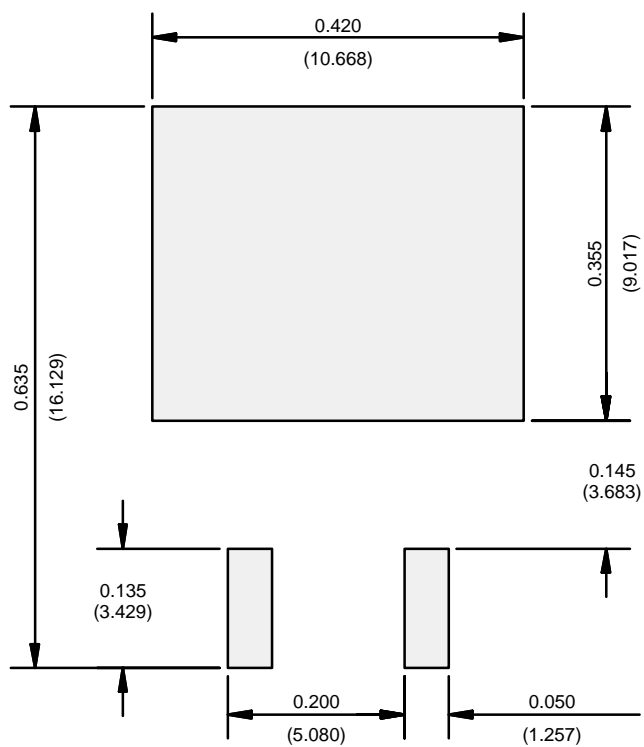
### Peak Diode Recovery dV/dt Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**

Recommended Minimum Pads  
Dimensions in Inches/(mm)

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